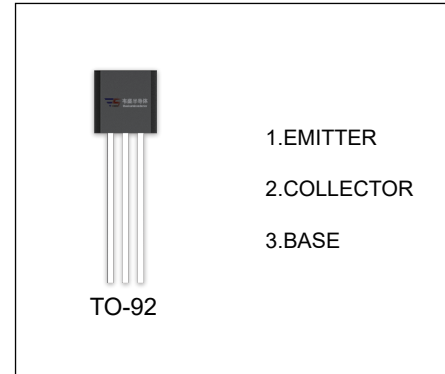


## 2SC2120 TRANSISTOR (NPN)

### FEATURES

- High DC Current Gain
- Complementary to 2SA950



### ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SC2120	TO-92	Bulk	1000pcs/Bag
2SC2120-TA	TO-92	Tape	2000pcs/Box

### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	35	V
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	0.8	A
P <sub>C</sub>	Collector Power Dissipation	600	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	208	°C /W
T <sub>J</sub> , T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~+150	°C

$T_a=25\text{ }^\circ\text{C}$  unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1\text{mA}, I_E=0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.1\text{mA}, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=35\text{V}, I_E=0$			0.1	$\mu\text{A}$
Collector cut-off current	$I_{CEO}$	$V_{CE}=25\text{V}, I_B=0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5\text{V}, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=1\text{V}, I_C=100\text{mA}$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=20\text{mA}$			0.5	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=1\text{V}, I_C=10\text{mA}$			0.8	V
Collector output capacitance	$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$			13	pF
Transition frequency	$f_T$	$V_{CE}=5\text{V}, I_C=10\text{mA}$	100			MHz

#### CLASSIFICATION OF $h_{FE}$

RANK	O	Y
RANGE	100-200	160-320

